



P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

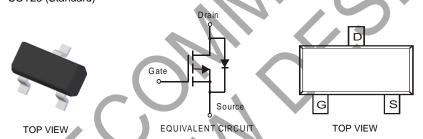
Features

- Low On-Resistance:
 - $R_{DS(ON)} < 100m\Omega @ V_{GS} = -4.5V, I_D = -2.7A$
 - $R_{DS(ON)} < 215m\Omega$ @ Vgs = -2.5V, ID = -2.0A
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Qsuffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotiveproducts/.
- This part is gualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23 (Standard)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2215L-7	SOT23 (Standard)	3000/Tape & Reel

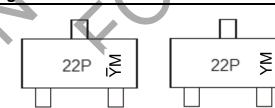
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



22P = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test Site) Y or \overline{Y} = Year (ex: I = 2021) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

Notes:

Year	2007		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	U			J	K	L	М	Ν	0	Р	R	S
Month	.lan	Feb	Mar	Anr	Mav	Jun	Jul.	Αυα	Sen	Oct	Nov	Dec
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			Vdss	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Drain Current (Note 5)	Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$		lр	-2.7 -2	A
Pulsed Drain Current (Note 6)			ldм	-8	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	1.08	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R _{0JA}	115	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	-20			V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS			-800	nA	$V_{DS} = -20V, V_{GS} = 0V$	
On-State Drain Current	I _{D(ON)}	-6			Α	$V_{DS} \leq \text{-}5V, \ V_{GS} = \text{-}4.5V$	
	ID(ON)	-3		—		$V_{DS} \leq -5V$, $V_{GS} = -2.5V$	
Gate-Source Leakage	Igss	—		±80	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	-0.45	—	-1.25	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
Static Drain-Source On-Resistance			80 165	100	mΩ	V _{GS} = -4.5V, I _D = -2.7A	
Static Drain-Source On-Resistance	R _{DS(ON)}			215		V _{GS} = -2.5V, I _D = -2.0A	
Forward Transfer Admittance	Y _{fs}		4	_	S	VDS = -5V, ID = -2.7A	
Diode Forward Voltage (Note 7)	Vsd	-		-1.26	V	$V_{GS} = 0V, I_{S} = -2.7A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		250		рF		
Output Capacitance	Coss		88	_	рF	Vps = -10V, Vgs = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	58	_	pF		
Gate Resistance	Rg		12	16	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$	
Total Gate Charge	Qg		4.3	5.3			
Gate-Source Charge	Q _{gs}		0.9	_	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -2.7A	
Gate-Drain Charge	Qgd		2.1			ID = -2.7A	

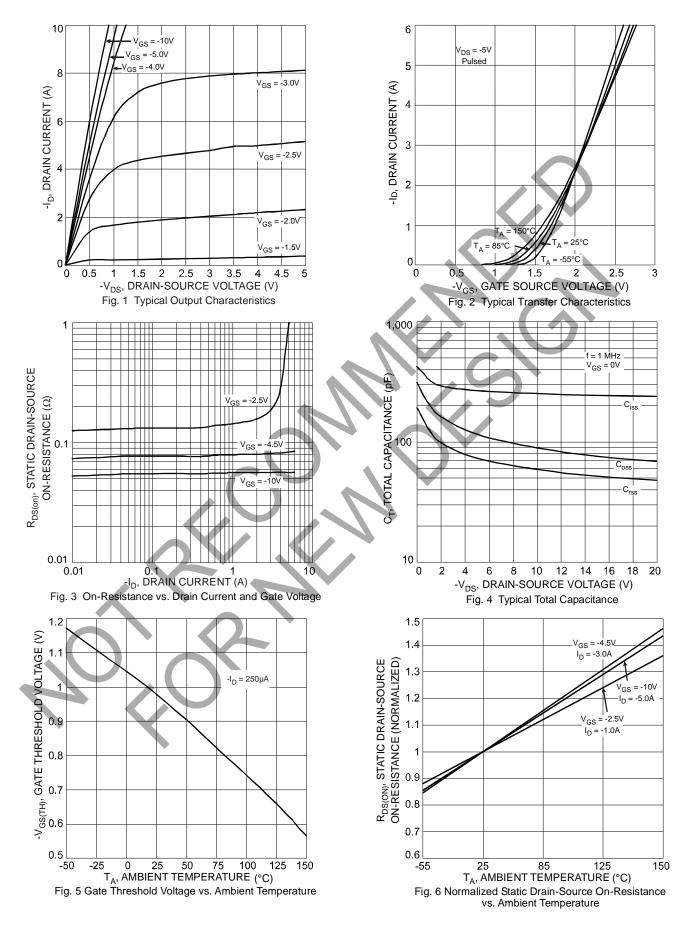
 Notes:
 5. Device mounted on FR-4 PCB. t ≤5 sec.

 6. Pulse width ≤10µS, Duty Cycle ≤1%.

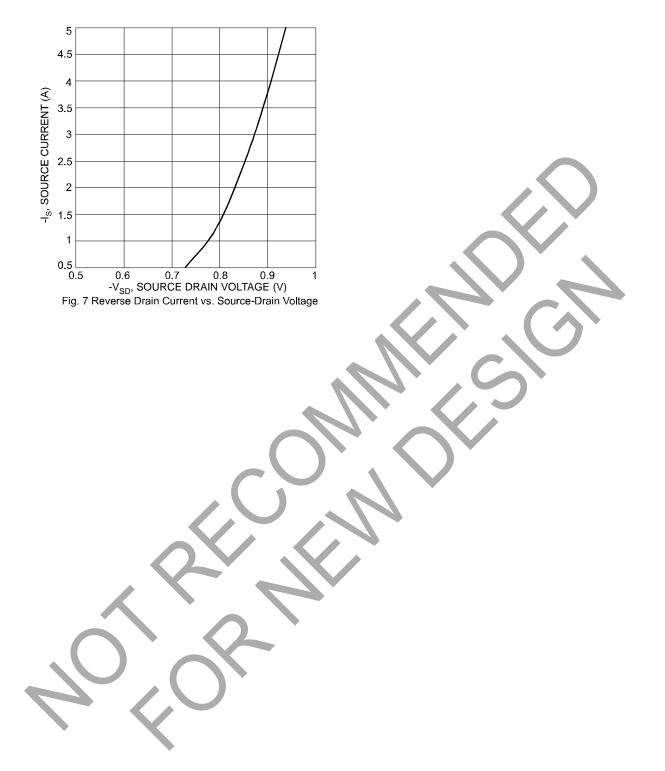
 7. Short duration pulse test used to minimize self-heating effect.

 8. Guaranteed by design. Not subject to product testing.





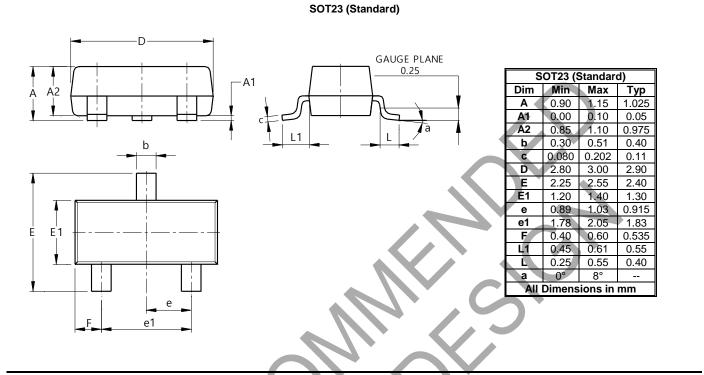






Package Outline Dimensions

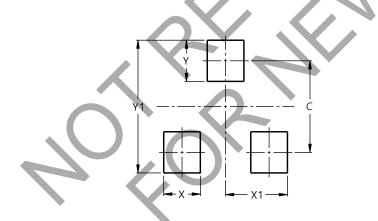
Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

Document number: DS31125 Rev. 10 - 3



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